

<small>Substitute for form 1449A/PTO</small>	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>	
(Use as many sheets as necessary)	
Sheet 1 of 2	
Attorney Docket No: 303.591US2	

US PATENT DOCUMENTS						
Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
KSS	US-3,665,241	05/23/1972	Spindt, C. A., et al.	313	351	07/13/1970
JM	US-3,755,704	08/28/1973	Spindt, Charles A., et al.	313	309	02/06/1970
JM	US-3,812,559	05/28/1974	Spindt, C. A., et al.	29	25.18	01/10/1972
JM	US-5,186,670	02/16/1993	Doan, T., et al.	445	24	03/02/1992
JM	US-5,229,331	07/20/1993	Doan, T., et al.	437	228	02/14/1992
JM	US-5,229,682	07/10/1993	Komatsu, Hiroshi	313	309	02/21/1992
JM	US-5,259,799	11/09/1993	Doan, T., et al.	445	24	11/17/1992
JM	US-5,358,908	10/25/1994	Reinberg, A. R., et al.	437	228	02/14/1992
JM	US-5,372,973	12/13/1994	Doan, T. T., et al.	437	228	04/27/1993
JM	US-5,401,676	03/28/1995	Lee, Kang-ok	437	200	08/30/1993
JM	US-5,458,518	10/17/1995	Lee, J. D.	445	24	11/07/1994
JM	US-5,564,958	10/15/1996	Itoh, S., et al.	445	6	05/09/1995
JM	US-5,578,902	11/26/1996	Vickers, K. G.	313	496	03/13/1995
JM	US-5,597,444	01/28/1997	Gilton, T. L.	156	643.1	01/29/1996
JM	US-5,608,283	03/04/1997	Twichell, J. C., et al.	313	309	06/29/1994
JM	US-5,627,427	05/06/1997	Das, John, et al.	313	308	06/05/1995
JM	US-5,653,619	08/05/1997	Cloud, E. H., et al.	445	24	09/06/1994
JM	US-5,666,020	09/09/1997	Takemura, Hisashi	313	306	11/16/1995
JM	US-5,672,938	09/30/1997	Jones, G. W.	313	504	09/27/1996
JM	US-5,769,679	06/23/1998	Park, Jong-Moon, et al.	445	50	09/18/1996
JM	US-5,844,250	12/01/1998	Itoh, , et al.	257	10	
JM	US-5,853,492	12/29/1998	Cathey, D. A., et al.	134	3	02/28/1996
JM	US-5,857,885	01/12/1999	Laou, Philips, et al.	445	24	11/04/1996
JM	US-5,898,258	04/27/1999	Sakai, T., et al.	313	309	01/24/1997
JM	US-5,910,791	06/08/1999	Zimlich, David, et al.	345	74	03/28/1996
JM	US-5,956,611	09/21/1999	Cathey, David, et al.	438	630	09/03/1997
JM	US-6,008,063	12/28/1999	Derra, Ammar	438	020	03/01/1999
JM	US-6,028,322	02/22/2000	Moradi, Behnam	257	010	07/22/1998
JM	US-6,080,032	06/27/2000	Alwan, J. J.	445	50	07/19/1999
JM	US-6,194,826	02/27/2001	Satou, Kazuya, et al.	313	485	03/11/1998
JM	US-6,232,705	05/15/2001	Forbes, L., et al.	313	309	09/01/1998
JM	US-6,323,587	11/27/2001	Zhang, T., et al.	313	309	08/06/1998

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T <sup>2</sup>

EXAMINER

Plenn M Zimmerman

DATE CONSIDERED

6/2/04

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 608. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. Applicant's unique citation designation number (optional):  Applicant is to place a check mark here if English language Translation is attached

K Suharay 4/5/07

<b>Substitute for form 1449A/PTO</b> <b>INFORMATION DISCLOSURE</b> <b>STATEMENT BY APPLICANT</b> <small>(Use as many sheets as necessary)</small>		Complete if Known Application Number      Unknown Filing Date      Even Date Herewith First Named Inventor      Moradi, Behnam Group Art Unit      Unknown Examiner Name      Ramsey, Kenneth	
		Sheet 2 of 2	
		Attorney Docket No: 303.591US2	

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No'	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T
DNY		ANDERSON, R. C., et al., "Porous Polycrystalline Silicon: A New Material for MEMS", IEEE, (1994), pp. 10-18	
DNY		BOSWELL, E. C., et al., "Polycrystalline Silicon Field Emitters", 8th International Vacuum Microelectronics Conference Technical Digest, (1996), pp. 181-185	
DNY		BOSWELL, E. C., et al., "Polycrystalline Silicon Field Emitters", J. Vac. Sci. Technol. B 14(3), (1996), pp. 1910-1913	
MNY		HUANG, W. N., et al., "Photoluminescence in porous sputtered polysilicon films formed by chemical etching", Semicond. Sci. Technol., 12, (1997), pp. 228-233	
MNY		HUANG, W. N., et al., "Properties of chemically etched porous polycrystalline silicon deposited by r.f. sputtering", IEEE Hong Kong Electron Devices Meeting, (1996), pp. 21-24	
MNY		HUQ, S. E., et al., "Comparative study of gated single crystal silicon and polysilicon field emitters", J. Vac. Sci. Technol. B 15(6), (1997), pp. 2855-2858	
DNY		HUQ, S. E., et al., "Fabrication of Gated Polycrystalline Silicon Field Emitters", 9th International Vacuum Microelectronics Conference, St. Petersburg, (1996), pp. 367-370	
MNY		KIM, I. H., et al., "Fabrication of metal field emitter arrays on polycrystalline silicon", J. Vac. Sci. Technol. B 15(2), (1997), pp. 468-471	
DNY		KIM, H., et al., "Metal FEA's on Double Layer Structure of Polycrystalline Silicon", 9th International Vacuum Microelectronics Conference, St. Petersburg, (1996), pp. 423-426	
DNY		LAZAROUK, S., et al., "Electrical characterization of visible emitting electroluminescent Schottky diodes based on n-type porous silicon and on highly doped n-type porous polysilicon", Journal of Non-Crystalline Solids, (1996), pp. 973-976	
MNY		LEE, J. H., et al., "A New Fabrication Method of Silicon Field Emitter Array with Local Oxidation of Polysilicon and Chemical-Mechanical-Polishing", 9th International Vacuum Microelectronics Conference, St. Petersburg, (1996), pp. 415-418	
MNY		PULLEN, S. E., et al., "Enhanced Field Emission from Polysilicon Emitters Using Porous Silicon", 9th International Vacuum Microelectronics Conference, St. Petersburg, (1996), pp. 211-214	
DNY		UH, H. S., et al., "Enhanced Electron Emission and Its Stability from Gated Mo-polyicide Field Emitters", IEEE, (1997), pp. 713-716	
MNY		UH, H. S., et al., "Fabrication and Characterization of Gated n Polycrystalline Silicon Field Emitter Arrays", 9th International Vacuum Microelectronics Conference, St. Petersburg, (1996), pp. 419-422	
DNY		UH, H. S., et al., "Process design and emission properties of gated n polycrystalline silicon field emitter arrays for flat-panel display applications", J. Vac. Sci. Technol. B 15(2), (1997), pp. 472-476	

EXAMINER

Munn M NY immersion

DATE CONSIDERED

6/2/04